

Notice of References Cited	Application/Control No. 09/912,558	Applicant(s)/Patent Under Reexamination WEIMER ET AL.	
	Examiner Erik Kielin	Art Unit 2813	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	C	US-2001/0020725	09-2001	Okuno et al.	257/410
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	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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	V	Lu et al. "Leakage current comparison between ultra-thin Ta2O5 films and conventional gate dielectrics" IEEE Electron Device Letters 19(9), 9/1998, pp. 341-342.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.